# Maja Buljan

List of Publications by Year
in descending order

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|---|---|---|---|
| 89 papers | 911 citations | 516710 16 h-index | 580821 25 g-index |
| 89 all docs | 89 docs citations | 89 times ranked | 912 citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Structural, Optical and Electrical Properties of Al+MoO3 and Au+MoO3 Thin Films Prepared by Magnetron Codeposition. Materials, 2021, 14, 766. | 2.9 | 2 |
| 2 | Hollow metal island films as plasmonic sensors produced by galvanic replacement. Surfaces and Interfaces, 2021, , 101483. | 3.0 | 2 |
| 3 | 3D networks of nanopores in alumina: Structural and optical properties. Microporous and Mesoporous Materials, 2021, 325, 111306. | 4.4 | 2 |
| 4 | Optical absorption in array of Ge/Al-shell nanoparticles in an Alumina matrix. Scientific Reports, 2020, 10, 65. | 3.3 | 7 |
| 5 | 3D Networks of Ge Quantum Wires in Amorphous Alumina Matrix. Nanomaterials, 2020, 10, 1363. | 4.1 | 8 |
| 6 | Deposition of Thin Alumina Films Containing 3D Ordered Network of Nanopores on Porous Substrates. Materials, 2020, 13, 2883. | 2.9 | 3 |
| 7 | Ge Quantum Dots Coated with Metal Shells (Al, Ta, and Ti) Embedded in Alumina Thin Films for Solar Energy Conversion. ACS Applied Nano Materials, 2020, 3, 8640-8650. | 5.0 | 10 |
| 8 | Ge quantum dot lattices in alumina prepared by nitrogen assisted deposition: Structure and photoelectric conversion efficiency. Solar Energy Materials and Solar Cells, 2020, 218, 110722. | 6.2 | 9 |
| 9 | Real-time tracking of the self-assembled growth of a 3D Ge quantum dot lattice in an alumina matrix. Journal of Applied Crystallography, 2020, 53, 1029-1038. | 4.5 | 3 |
| 10 | Impact of the Zn source on the RSN-type zeolite formation. Inorganic Chemistry Frontiers, 2019, 6, 2279-2290. | 6.0 | 5 |
| 11 | Application of GISAXS in the Investigation of Three-Dimensional Lattices of Nanostructures. Crystals, 2019, 9, 479. | 2.2 | 14 |
| 12 | Studies of bronze corrosion phenomena by EBS and complementary techniques. Nuclear Instruments & Methods in Physics Research B, 2019, 461, 154-158. | 1.4 | 1 |
| 13 | $ ewcommand{t}{eta} t$ -TaON thin films: production by reactive magnetron sputtering and the question of non-stoichiometry. Journal Physics D: Applied Physics, 2019, 52, 305304. | 2.8 | 5 |
| 14 | Preparation of non-oxidized Ge quantum dot lattices in amorphous Al<sub>2</sub>O<sub>3</sub>, Si<sub>3</sub>N<sub>4</sub> and SiC matrices. Nanotechnology, 2019, 30, 335601. | 2.6 | 14 |
| 15 | Influence of Structure on Electronic Charge Transport in 3D Ge Nanowire Networks in an Alumina Matrix. Scientific Reports, 2019, 9, 5432. | 3.3 | 4 |
| 16 | Infrared spectroscopy of ion tracks in amorphous SiO2 and comparison to gamma irradiation induced changes. Journal of Nuclear Materials, 2019, 514, 74-83. | 2.7 | 8 |
| 17 | Evaluating Automatic Term Extraction Methods on Individual Documents. , 2019, , . | | 10 |
| 18 | Recent developments in surface science and engineering, thin films, nanoscience, biomaterials, plasma science, and vacuum technology. Thin Solid Films, 2018, 660, 120-160. | 1.8 | 27 |

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|---|---|---|---|
| 19 | Kinetic Monte Carlo simulation of growth of Ge quantum dot multilayers with amorphous matrix. Journal of Nanoparticle Research, 2017, 19, 1. | 1.9 | 2 |
| 20 | Temperature behaviour of the average size of nanoparticle lattices co-deposited with an amorphous matrix. Analysis of Ge + Al2O3and Ni + Al2O3thin films. Journal of Physics Condensed Matter, 2017, 29, 435301. | 1.8 | 0 |
| 21 | Annealing induced semiconductor-metal transition in Ge+ITO film. Applied Physics Letters, 2017, 111, 172104. | 3.3 | 3 |
| 22 | GISAXS analysis of ion beam modified films and surfaces. Computer Physics Communications, 2017, 212, 69-81. | 7.5 | 4 |
| 23 | Ta2N3 nanocrystals grown in Al2O3 thin layers. Beilstein Journal of Nanotechnology, 2017, 8, 2162-2170. | 2.8 | 2 |
| 24 | Ge/Si core/shell quantum dots in alumina: tuning the optical absorption by the core and shell size. Nanophotonics, 2017, 6, 1055-1062. | 6.0 | 22 |
| 25 | Modification of semiconductor or metal nanoparticle lattices in amorphous alumina by MeV heavy ions. New Journal of Physics, 2016, 18, 093032. | 2.9 | 6 |
| 26 | Formation of swift heavy ion tracks on a rutile TiO<sub>2</sub> (001) surface. Journal of Applied Crystallography, 2016, 49, 1704-1712. | 4.5 | 18 |
| 27 | Closely packed Ge quantum dots in ITO matrix: influence of Ge crystallization on optical and electrical properties. Materials Research Express, 2016, 3, 065003. | 1.6 | 3 |
| 28 | Self-assembly of Ge quantum dots on periodically corrugated Si surfaces. Applied Physics Letters, 2015, 107, 203101. | 3.3 | 5 |
| 29 | Structural characterization of quantum dot lattices by GISAXS: models and software packageGisaxStudio. Acta Crystallographica Section A: Foundations and Advances, 2015, 71, s378-s378. | 0.1 | 0 |
| 30 | Production of three-dimensional quantum dot lattice of Ge/Si coreâ€“shell quantum dots and Si/Ge layers in an alumina glass matrix. Nanotechnology, 2015, 26, 065602. | 2.6 | 16 |
| 31 | Response of GaN to energetic ion irradiation: conditions for ion track formation. Journal Physics D: Applied Physics, 2015, 48, 325304. | 2.8 | 40 |
| 32 | Evolution of the surface plasmon resonance of Au:TiO2 nanocomposite thin films with annealing temperature. Journal of Nanoparticle Research, 2014, 16, 1. | 1.9 | 27 |
| 33 | Compositionally modulated ripples during composite film growth: Three-dimensional pattern formation at the nanoscale. Physical Review B, 2014, 89, . | 3.2 | 12 |
| 34 | Effect of bi-layer ratio in ZnO/Al2O3 multilayers on microstructure and functional properties of ZnO nanocrystals embedded in Al2O3 matrix. Applied Physics A: Materials Science and Processing, 2014, 115, 283-289. | 2.3 | 9 |
| 35 | Self-assembled growth of Ni nanoparticles in amorphous alumina matrix. Journal of Nanoparticle Research, 2014, 16, 1. | 1.9 | 7 |
| 36 | Recent advances in vacuum sciences and applications. Journal Physics D: Applied Physics, 2014, 47, 153001. | 2.8 | 33 |

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|---|---|---|---|
| 37 | Fe2O3/TiO2 nanoparticlesâ€"a complex structural study. Thin Solid Films, 2014, 564, 65-72. | 1.8 | 3 |
| 38 | Magnetic properties of nickel nanoparticles embedded in amorphous Al2O3matrix. Journal of Physics: Conference Series, 2014, 568, 042022. | 0.4 | 0 |
| 39 | Ge quantum dot lattices in Al2O3 multilayers. Journal of Nanoparticle Research, 2013, 15, 1. | 1.9 | 27 |
| 40 | Charge storage behavior of nanostructures based on SiGe nanocrystals embedded in Al2O3 matrix. European Physical Journal B, 2013, 86, 1. | 1.5 | 5 |
| 41 | Influence of RF-sputtering power on formation of vertically stacked Si<sub>1â^'x</sub>Ge<sub>x</sub>nanocrystals between ultra-thin amorphous Al<sub>2</sub>O<sub>3</sub>layers: structural and photoluminescence properties. Journal Physics D: Applied Physics, 2013, 46, 385301. | 2.8 | 1 |
| 42 | Tuning the growth properties of Ge quantum dot lattices in amorphous oxides by matrix type. Journal of Applied Crystallography, 2013, 46, 1490-1500. | 4.5 | 16 |
| 43 | Growth of a three-dimensional anisotropic lattice of Ge quantum dots in an amorphous alumina matrix. Journal of Applied Crystallography, 2013, 46, 709-715. | 4.5 | 8 |
| 44 | Materials modification using ions with energies below 1MeV/u. Nuclear Instruments & Methods in Physics Research B, 2013, 317, 143-148. | 1.4 | 3 |
| 45 | X-ray small-angle scattering from sputtered CeO2/C bilayers. Journal of Applied Physics, 2013, 113, 024301. | 2.5 | 0 |
| 46 | Co nanocrystals in amorphous multilayers â€" a structure study. Journal of Applied Crystallography, 2013, 46, 1711-1721. | 4.5 | 5 |
| 47 | Influence of annealing conditions on the structural and photoluminescence properties of Ge quantum dot lattices in a continuous Geâ€‰+â€‰Al2 O3 film. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 1516-1521. | 1.8 | 2 |
| 48 | Determination of ion track radii in amorphous matrices via formation of nano-clusters by ion-beam irradiation. Applied Physics Letters, 2012, 101, 103112. | 3.3 | 10 |
| 49 | Tuning the properties of Ge-quantum dots superlattices in amorphous silica matrix through deposition conditions. Journal of Applied Physics, 2012, 111, 074316. | 2.5 | 4 |
| 50 | Influence of annealing conditions on the formation of regular lattices of voids and Ge quantum dots in an amorphous alumina matrix. Nanotechnology, 2012, 23, 405605. | 2.6 | 8 |
| 51 | Structural and electrical studies of ultrathin layers with Si0.7Ge0.3 nanocrystals confined in a SiGe/SiO2 superlattice. Journal of Applied Physics, 2012, 111, 104323. | 2.5 | 10 |
| 52 | Conditions for formation of germanium quantum dots in amorphous matrices by MeV ions: Comparison with standard thermal annealing. Physical Review B, 2012, 86, . | 3.2 | 15 |
| 53 | Grazing-incidence small-angle X-ray scattering: application to the study of quantum dot lattices. Acta Crystallographica Section A: Foundations and Advances, 2012, 68, 124-138. | 0.3 | 61 |
| 54 | Structural and morphological properties of Fe2O3/TiO2 nanocrystals in silica matrix. Thin Solid Films, 2012, 520, 4800-4802. | 1.8 | 1 |

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|---|---|---|---|
| 55 | Preparation of regularly ordered Ge quantum dot lattices in amorphous matrices. Vacuum, 2012, 86, 733-736. | 3.5 | 6 |
| 56 | X-ray characterization of semiconductor nanostructures. Semiconductor Science and Technology, 2011, 26, 064002. | 2.0 | 2 |
| 57 | Characterisation of thin LPCVD silicon-rich oxide films. Proceedings of SPIE, 2011, , . | 0.8 | 0 |
| 58 | Design of quantum dot lattices in amorphous matrices by ion beam irradiation. Physical Review B, 2011, 84, . | 3.2 | 16 |
| 59 | Low-temperature fabrication of layered self-organized Ge clusters by RF-sputtering. Nanoscale Research Letters, 2011, 6, 341. | 5.7 | 18 |
| 60 | Surface characterization of thin silicon-rich oxide films. Journal of Molecular Structure, 2011, 993, 214-218. | 3.6 | 6 |
| 61 | Influence of the deposition parameters on the growth of SiGe nanocrystals embedded in Al2O3 matrix. Microelectronic Engineering, 2011, 88, 509-513. | 2.4 | 8 |
| 62 | Ellipsometric study of thermally induced redistribution and crystallization of Ge in Ge:SiO2 mixture layers. Thin Solid Films, 2011, 519, 5419-5423. | 1.8 | 2 |
| 63 | Electrical Characterization of Ge Nanocrystals in Oxide Matrix. Materials Research Society Symposia Proceedings, 2011, 1305, 1. | 0.1 | 0 |
| 64 | Multilayers of Ge nanocrystals embedded in Al2O3 matrix: Structural and electrical studies. Microelectronic Engineering, 2010, 87, 2508-2512. | 2.4 | 8 |
| 65 | Structural study of Si1â^'xGex nanocrystals embedded in SiO2 films. Thin Solid Films, 2010, 518, 2569-2572. | 1.8 | 9 |
| 66 | Structural and charge trapping properties of two bilayer (Ge+SiO2)/SiO2 films deposited on rippled substrate. Applied Physics Letters, 2010, 97, 163117. | 3.3 | 17 |
| 67 | Growth of spatially ordered Ge nanoclusters in an amorphous matrix on rippled substrates. Physical Review B, 2010, 82, . | 3.2 | 9 |
| 68 | Formation of void lattice after annealing of Ge quantum dot lattice in alumina matrix. Applied Physics Letters, 2010, 97, . | 3.3 | 13 |
| 69 | Self-assembling of Ge quantum dots in an alumina matrix. Physical Review B, 2010, 82, . | 3.2 | 26 |
| 70 | Generation of an ordered Ge quantum dot array in an amorphous silica matrix by ion beam irradiation: Modeling and structural characterization. Physical Review B, 2010, 81, . | 3.2 | 17 |
| 71 | Formation of three-dimensional quantum-dot superlattices in amorphous systems: Experiments and Monte Carlo simulations. Physical Review B, 2009, 79, . | 3.2 | 57 |
| 72 | Formation of long-range ordered quantum dots arrays in amorphous matrix by ion beam irradiation. Applied Physics Letters, 2009, 95, 063104. | 3.3 | 24 |

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|---|---|---|---|
| 73 | Size and spatial homogeneity of SiGe quantum dots in amorphous silica matrix. Journal of Applied Physics, 2009, 106, 084319. | 2.5 | 11 |
| 74 | The influence of deposition temperature on the correlation of Ge quantum dot positions in amorphous silica matrix. Nanotechnology, 2009, 20, 085612. | 2.6 | 35 |
| 75 | Grazing incidence X-ray study of Ge-nanoparticle formation in (Ge:SiO2)/SiO2 multilayers. Thin Solid Films, 2009, 517, 1899-1903. | 1.8 | 10 |
| 76 | Crystal structure of defect-containing semiconductor nanocrystals â€“ an X-ray diffraction study. Journal of Applied Crystallography, 2009, 42, 660-672. | 4.5 | 6 |
| 77 | Complementary application of Raman scattering and GISAXS in characterization of embedded semiconductor QDs. Superlattices and Microstructures, 2008, 44, 385-394. | 3.1 | 0 |
| 78 | Formation of Ge-nanocrystals in SiO2 matrix by magnetron sputtering and post-deposition thermal treatment. Superlattices and Microstructures, 2008, 44, 323-330. | 3.1 | 11 |
| 79 | Raman scattering on quadrupolar vibrational modes of spherical nanoparticles. Journal of Applied Physics, 2008, 104, . | 2.5 | 6 |
| 80 | Implantation conditions for diamond nanocrystal formation in amorphous silica. Journal of Applied Physics, 2008, 104, 034315. | 2.5 | 2 |
| 81 | Transmission electron microscopy study of carbon nanophases produced by ion beam implantation. Materials Science and Engineering C, 2006, 26, 1202-1206. | 7.3 | 6 |
| 82 | Ion beam synthesis and characterization of Ge nanoparticles in SiO2. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 843-846. | 1.4 | 11 |
| 83 | The evolution of the morphology of Ge nanocrystals formed by ion implantation in SiO2. Nuclear Instruments & Methods in Physics Research B, 2005, 238, 272-275. | 1.4 | 4 |
| 84 | Influence of stoichiometry deviations on properties of ion-beam synthesized CdSe QDs. Nuclear Instruments & Methods in Physics Research B, 2005, 238, 302-305. | 1.4 | 7 |
| 85 | Direct ion beam synthesis of IIâ€“VI nanocrystals. Nuclear Instruments & Methods in Physics Research B, 2004, 216, 407-413. | 1.4 | 11 |
| 86 | GISAXS studies of morphology and size distribution of CdS nanocrystals formed in SiO2 by ion implantation. Nuclear Instruments & Methods in Physics Research B, 2003, 200, 191-195. | 1.4 | 7 |
| 87 | Analysis of 2D GISAXS patterns obtained on semiconductor nanocrystals. Vacuum, 2003, 71, 65-70. | 3.5 | 12 |
| 88 | Ion beam synthesis of buried Zn-VI quantum dots in SiO2â€“ grazing incidence small-angle X-ray scattering studies. Journal of Applied Crystallography, 2003, 36, 439-442. | 4.5 | 6 |
| 89 | Grazing incidence small-angle X-ray scattering studies of the synthesis and growth of CdS quantum dots from constituent atoms in SiO2matrix. Journal of Applied Crystallography, 2003, 36, 443-446. | 4.5 | 6 |